Kazutoshi Kojima

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

131 papers	1,809 citations	20 h-index	36 g-index
135 ext. papers	1,964 ext. citations	1.3 avg, IF	4.18 L-index

#	Paper	IF	Citations
131	SiC p+n Junction-Diodes toward Beam Monitor Applications. *IEEE Transactions on Nuclear Science*, **2021**, 1-1	1.7	1
130	Carrier dynamics of silicon vacancies of SiC under simultaneous optically and electrically excitations. *Applied Physics Letters*, **2021**, 118, 021106	3.4	1
129	Thermometric quantum sensor using excited state of silicon vacancy centers in 4H-SiC devices. *Applied Physics Letters*, **2021**, 118, 044001	3.4	3
128	Investigation of Factors Influencing the Occurrence of 3C-Inclusions for the Thick Growth of on-Axis C-Face 4H-SiC Epitaxial Layers. *Materials*, **2020**, 13,	3.5	1
127	Development of 4H-SiC Schottky np diode with high blocking voltage and ultralow on-resistance. *Applied Physics Letters*, **2020**, 116, 012103	3.4	7
126	Nondestructive measurements of depth distribution of carrier lifetimes in 4H-SiC thick epitaxial layers using time-resolved free carrier absorption with intersectional lights. *Review of Scientific Instruments*, **2020**, 91, 123902	1.7	0
125	Observation of carrier lifetime distribution in 4H-SiC thick epilayers using microscopic time-resolved free carrier absorption system. *Journal of Applied Physics*, **2020**, 128, 105702	2.5	2
124	Influence of basal-plane dislocation structures on expansion of single Shockley-type stacking faults in forward-current degradation of 4H-SiC pin diodes. *Japanese Journal of Applied Physics*, **2018**, 57, 04FR07	1.4	15
123	Ammonia-free high temperature metalorganic vapor phase epitaxy (AFHT-MOVPE): a new approach to high quality AlN growth. *CrystEngComm*, **2018**, 20, 7364-7370	3.3	8
122	Strong impact of slight trench direction misalignment from $[11bar{2}0]$ on deep trench filling epitaxy for SiC super-junction devices. *Japanese Journal of Applied Physics*, **2017**, 56, 04CR05	1.4	14
121	Reduction of background carrier concentration and lifetime improvement for 4H-SiC C-face epitaxial growth. *Japanese Journal of Applied Physics*, **2017**, 56, 081302	1.4	3
120	Characterization of stacking faults with emission wavelengths of over 500 nm formed in 4H-SiC epitaxial films. *Journal of Crystal Growth*, **2017**, 476, 99-106	1.6	1
119	Origin analysis of expanded stacking faults by applying forward current to 4H-SiC pin diodes. *Applied Physics Express*, **2017**, 10, 081201	2.4	11
118	Investigation of Low Off-Angled 4H-SiC Epitaxial Wafers for Power Device Applications. *ECS Journal of Solid State Science and Technology*, **2017**, 6, P547-P552	2	0
117	An empirical growth window concerning the input ratio of HCl/SiH4gases in filling 4H-SiC trench by CVD. *Applied Physics Express*, **2017**, 10, 055505	2.4	9
116	Study of spiral growth on 4H-silicon carbide on-axis substrates. *Journal of Crystal Growth*, **2017**, 475, 251-255	1.6	2
115	Electrical and physical characterizations of the effects of oxynitridation and wet oxidation at the interface of SiO2/4H-SiC(0001) and $(000bar{1})$. *Japanese Journal of Applied Physics*, **2016**, 55, 04ER19	1.4	5

114	Numerical analysis of the Gibbs–Thomson effect on trench-filling epitaxial growth of 4H-SiC. *Applied Physics Express*, **2016**, 9, 035601	2.4	8
113	Influence of growth pressure on filling 4H-SiC trenches by CVD method. *Japanese Journal of Applied Physics*, **2016**, 55, 01AC04	1.4	5
112	Development of diagnostic method for deep levels in semiconductors using charge induced by heavy ion microbeams. *Nuclear Instruments & Methods in Physics Research B*, **2015**, 348, 240-245	1.2	5
111	Filling 4H-SiC trench towards selective epitaxial growth by adding HCl to CVD process. *Applied Physics Express*, **2015**, 8, 065502	2.4	13
110	Epitaxial growth and characterization of thick multi-layer 4H-SiC for very high-voltage insulated gate bipolar transistors. *Journal of Applied Physics*, **2015**, 118, 085702	2.5	11
109	Systematic investigation on in-plane anisotropy of surface and buried channel mobility of metal-oxide-semiconductor field-effect-transistors on Si-, a-, and m-face 4H-SiC. *Applied Physics Letters*, **2015**, 106, 103506	3.4	7
108	Synchrotron X-ray topography analysis of local damage occurring during polishing of 4H-SiC wafers. *Japanese Journal of Applied Physics*, **2015**, 54, 091301	1.4	9
107	Experiment on alleviating the bending of CVD-grown heavily Al-doped 4H-SiC epiwafer by codoping of N. *Japanese Journal of Applied Physics*, **2015**, 54, 04DP08	1.4	4
106	Hopping conduction range of heavily Al-doped 4H-SiC thick epilayers grown by CVD. *Applied Physics Express*, **2015**, 8, 121302	2.4	8
105	Homoepitaxial growth and investigation of stacking faults of 4H-SiC C-face epitaxial layers with a 1° off-angle. *Japanese Journal of Applied Physics*, **2015**, 54, 04DP04	1.4	6
104	Linear energy transfer dependence of single event gate rupture in SiC MOS capacitors. *Nuclear Instruments & Methods in Physics Research B*, **2014**, 319, 75-78	1.2	13
103	Suppression of short step bunching generated on 4H-SiC Si-face substrates with vicinal off-angle. *Journal of Crystal Growth*, **2014**, 401, 673-676	1.6	7
102	Development of SiC Super-Junction (SJ) Devices by Multi-Epitaxial Growth. *Materials Science Forum*, **2014**, 778-780, 845-850	0.4	20
101	Threshold Voltage Instability of SiC-MOSFETs on Various Crystal Faces. *Materials Science Forum*, **2014**, 778-780, 521-524	0.4	14
100	Suppression of 3-Inclusion Formation during Growth of 4-SiC Si-Face Homoepitaxial Layers with a 1° Off-Angle. *Materials*, **2014**, 7, 7010-7021	3.5	6
99	Development of Homoepitaxial Growth Technique on 4H-SiC Vicinal Off Angled Substrate. *Materials Science Forum*, **2014**, 778-780, 125-130	0.4	1
98	Epitaxial Growth of Thick Multi-Layer 4H-SiC for the Fabrication of Very High-Voltage C-Face n-Channel IGBT. *Materials Science Forum*, **2014**, 778-780, 135-138	0.4	8
97	Homo-Epitaxial Growth on 2° Off-Cut 4H-SiC(0001) Si-Face Substrates Using H2-SiH4-C3H8 CVD System. *Materials Science Forum*, **2014**, 778-780, 214-217	0.4	5

96	Conversion of Basal Plane Dislocations to Threading Edge Dislocations in Growth of Epitaxial Layers on 4H-SiC Substrates with a Vicinal Off-Angle. *Materials Science Forum*, **2014**, 778-780, 99-102	0.4	4
95	Analysis on Generation of Localized Step-Bunchings on 4H-SiC(0001)Si Face by Synchrotron X-Ray Topography. *Materials Science Forum*, **2014**, 778-780, 398-401	0.4	13
94	Carrier Density Dependence of Fano Type Interference in Raman Spectra of p-type 4H-SiC. *Materials Science Forum*, **2014**, 778-780, 475-478	0.4	9
93	Dependence of the Growth Parameters on the In-Plane Distribution of 150 mm Size SiC Epitaxial Wafer. *Materials Science Forum*, **2014**, 778-780, 139-142	0.4	
92	Microstructural Analysis of Damaged Layer Introduced during Chemo-Mechanical Polishing. *Materials Science Forum*, **2014**, 778-780, 370-373	0.4	14
91	Characterization of the Defect Evolution in Thick Heavily Al-Doped 4H-SiC Epilayers. *Materials Science Forum*, **2014**, 778-780, 151-154	0.4	3
90	C-Face Epitaxial Growth of 4H-SiC on Quasi-150-mm Diameter Wafers with High Throughput. *Materials Science Forum*, **2014**, 778-780, 109-112	0.4	4
89	Suppressing Al memory effect on CVD growth of 4H-SiC epilayers by adding hydrogen chloride gas. *Japanese Journal of Applied Physics*, **2014**, 53, 04EP07	1.4	1
88	Defect-induced performance degradation of 4H-SiC Schottky barrier diode particle detectors. *Journal of Applied Physics*, **2013**, 113, 143714	2.5	24
87	The Growth of 3-Inch 4H-SiC Si-Face Epitaxial Wafer with Vicinal Off-Angle. *Materials Science Forum*, **2013**, 740-742, 193-196	0.4	7
86	The growth of low resistivity, heavily Al-doped 4H-SiC thick epilayers by hot-wall chemical vapor deposition. *Journal of Crystal Growth*, **2013**, 380, 85-92	1.6	30
85	Development of SiC Super-Junction (SJ) Device by Deep Trench-Filling Epitaxial Growth. *Materials Science Forum*, **2013**, 740-742, 785-788	0.4	21
84	Growth of silicon carbide epitaxial layers on 150-mm-diameter wafers using a horizontal hot-wall chemical vapor deposition. *Journal of Crystal Growth*, **2013**, 381, 139-143	1.6	10
83	Filling of Deep Trench by Epitaxial SiC Growth. *Materials Science Forum*, **2013**, 740-742, 793-796	0.4	13
82	Electrical Properties of MOS Structures on 4H-SiC (11-20) Face. *Materials Science Forum*, **2013**, 740-742, 621-624	0.4	6
81	4H-SiC Homoepitaxial Growth on Substrate with Vicinal Off-Angle Lower than 1° *ECS Journal of Solid State Science and Technology*, **2013**, 2, N3012-N3017	2	15
80	Low Resistivity, Thick Heavily Al-Doped 4H-SiC Epilayers Grown by Hot-Wall Chemical Vapor Deposition. *Materials Science Forum*, **2013**, 740-742, 181-184	0.4	18
79	Suppression of Al Memory-Effect on Growing 4H-SiC Epilayers by Hot-Wall Chemical Vapor Deposition. *Japanese Journal of Applied Physics*, **2013**, 52, 04CP04	1.4	1

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78	E1/E2 traps in 6H-SiC studied with Laplace deep level transient spectroscopy. *Applied Physics Letters*, **2013**, 102, 032104	3.4	11
77	Improvement of Homoepitaxial Layer Quality Grown on 4H-Si□Si-Face Substrate Lower than 1 Degree Off Angle. *Materials Science Forum*, **2012**, 717-720, 141-144	0.4	6
76	Peak Degradation of Heavy-Ion Induced Transient Currents in 6H-SiC MOS Capacitors. *Materials Science Forum*, **2012**, 717-720, 469-472	0.4	
75	Effect of Post-Oxidation Annealing in Wet O2 and N2O Ambient on Thermally Grown SiO2/4H-SiC Interface for P-Channel MOS Devices. *Materials Science Forum*, **2012**, 717-720, 709-712	0.4	6
74	Defects in an Electron-Irradiated 6H-SiC Diode Studied by Alpha Particle Induced Charge Transient Spectroscopy: Their Impact on the Degraded Charge Collection Efficiency. *Materials Science Forum*, **2012**, 717-720, 267-270	0.4	
73	Determination of carrier concentration by Fano interference of Raman scattering in heavily doped n-type 4H-SiC. *Journal of Applied Physics*, **2012**, 112, 043514	2.5	18
72	Challenges of High-Performance and High-Reliablity in SiC MOS Structures. *Materials Science Forum* , **2012**, 717-720, 703-708	0.4	19
71	Reducing Stacking Faults in Highly Doped N-Type 4H-SiC Crystal. *Materials Science Forum*, **2011**, 679-680, 8-11	0.4	11
70	Single-Alpha-Particle-Induced Charge Transient Spectroscopy of the 6H-SiC ${hbox{p}}^{+}{hbox{n}}$ Diode Irradiated With High-Energy Electrons. *IEEE Transactions on Nuclear Science*, **2011**, 58, 3328-3332	1.7	3
69	Transient Analysis of an Extended Drift Region in a 6H-SiC Diode Formed by a Single Alpha Particle Strike and Its Contribution to the Increased Charge Collection. *IEEE Transactions on Nuclear Science*, **2011**, 58, 305-313	1.7	9
68	Oxygen Ion Induced Charge in SiC MOS Capacitors Irradiated with Gamma-Rays. *Materials Science Forum*, **2011**, 679-680, 362-365	0.4	1
67	Isotropic Channel Mobility in UMOSFETs on 4H-SiC C-Face with Vicinal Off-Angle. *Materials Science Forum*, **2010**, 645-648, 999-1004	0.4	22
66	4H-SiC Homoepitaxial Growth on Vicinal-Off Angled Si-Face Substrate. *Materials Science Forum*, **2010**, 645-648, 99-102	0.4	8
65	Charge Collection Efficiency of 6H-SiC P+N Diodes Degraded by Low-Energy Electron Irradiation. *Materials Science Forum*, **2010**, 645-648, 921-924	0.4	6
64	Charge Enhancement Effects in 6H-SiC MOSFETs Induced by Heavy Ion Strike. *IEEE Transactions on Nuclear Science*, **2010**,	1.7	4
63	Doping Concentration Optimization for Ultra-Low-Loss 4H-SiC Floating Junction Schottky Barrier Diode (Super-SBD). *Materials Science Forum*, **2009**, 615-617, 655-658	0.4	6
62	Charge Collection Properties of 6H-SiC Diodes by Wide Variety of Charged Particles up to Several Hundreds MeV. *Materials Science Forum*, **2009**, 615-617, 861-864	0.4	6
61	Transient Currents Induced in 6H-SiC MOS Capacitors by Oxygen Ion Incidence. *Materials Science Forum*, **2009**, 615-617, 517-520	0.4	5

60	Evaluation of 4H-SiC Thermal Oxide Reliability Using Area-Scaling Method. *Japanese Journal of Applied Physics*, **2009**, 48, 081404	1.4	18
59	Control of the Surface Morphology on Low Off Angled 4H-SiC Homoepitaxal Growth. *Materials Science Forum*, **2009**, 615-617, 113-116	0.4	9
58	Ultralow-Loss SiC Floating Junction Schottky Barrier Diodes (Super-SBDs). *IEEE Transactions on Electron Devices*, **2008**, 55, 1954-1960	2.9	23
57	Transient Response to High Energy Heavy Ions in 6H-SiC n+p Diodes. *Materials Science Forum*, **2008**, 600-603, 1039-1042	0.4	
56	Gate-Area Dependence of SiC Thermal Oxides Reliability. *Materials Science Forum*, **2008**, 600-603, 787-790	0.4	1
55	Characterization of Electrical Properties in SiC Crystals by Raman Scattering Spectroscopy. *Materials Science Forum*, **2008**, 600-603, 501-504	0.4	3
54	Challenges of 4H-SiC MOSFETs on the C(000-1) Face toward the Achievement of Ultra Low On-Resistance. *Materials Science Forum*, **2008**, 600-603, 907-912	0.4	
53	Effects of Fabrication Process on the Electrical Characteristics of n-Channel MOSFETs Irradiated with Gamma-Rays. *Materials Science Forum*, **2008**, 600-603, 707-710	0.4	
52	Determination of free carrier density in the low doping regime of 4H-SiC by Raman scattering. *Applied Physics Letters*, **2008**, 93, 121913	3.4	16
51	Decrease of Charge Collection Due to Displacement Damage by Gamma Rays in a 6H-SiC Diode. *IEEE Transactions on Nuclear Science*, **2007**, 54, 1953-1960	1.7	12
50	Influence of Micropipe and Domain Boundary in SiC Substrate on the DC Characteristics of AlGaN/GaN HFET. *Materials Science Forum*, **2007**, 556-557, 1043-1046	0.4	1
49	Effect of Additional Silane on In Situ H2 Etching prior to 4H-SiC Homoepitaxial Growth. *Materials Science Forum*, **2007**, 556-557, 85-88	0.4	20
48	Simulation, Fabrication and Characterization of 4H-SiC Floating Junction Schottky Barrier Diodes (Super-SBDs). *Materials Science Forum*, **2007**, 556-557, 881-884	0.4	7
47	Influence of lattice polarity of nitrogen and aluminum doping on 4H-SiC epitaxial layer. *Microelectronic Engineering*, **2006**, 83, 79-81	2.5	10
46	Homoepitaxial Growth on a 4H-SiC C-Face Substrate. *Chemical Vapor Deposition*, **2006**, 12, 489-494		8
45	Investigation of In-Grown Dislocations in 4H-SiC Epitaxial Layers. *Materials Science Forum*, **2006**, 527-529, 147-152	0.4	7
44	Fabrication of 4H-SiC Floating Junction Schottky Barrier Diodes (Super-SBDs) and their Electrical Properties. *Materials Science Forum*, **2006**, 527-529, 1175-1178	0.4	10
43	High Inversion Channel Mobility of 4H-SiC MOSFETs Fabricated on C(000-1) Epitaxial Substrate with Vicinal (Below 1[illegible]) Off-Angle. *Materials Science Forum*, **2006**, 527-529, 1043-1046	0.4	8

42	Effect of Surface Orientation and Off-Angle on Surface Roughness and Electrical Properties of p-Type Impurity Implanted 4H-SiC Substrate after High Temperature Annealing. *Materials Science Forum*, **2006**, 527-529, 835-838	0.4	2
41	Correlation between reliability of thermal oxides and dislocations in n-type 4H-SiC epitaxial wafers. *Applied Physics Letters*, **2006**, 89, 022909	3.4	55
40	Nitrogen incorporation characteristics on a 4H-SiC epitaxial layer. *Applied Physics Letters*, **2006**, 88, 021907	3.4	11
39	Effect of growth condition on micropipe filling of 4H-SiC epitaxial layer. *Journal of Crystal Growth*, **2005**, 275, e549-e554	1.6	19
38	Modeling of SiC-CVD on Si-face/C-face in a horizontal hot-wall reactor. *Journal of Crystal Growth*, **2005**, 275, e515-e520	1.6	12
37	Epitaxial Overgrowth of 4H-SiC for Devices with p-Buried Floating Junction Structure. *Materials Science Forum*, **2005**, 483-485, 147-150	0.4	3
36	2-Inch 4H-SiC Homoepitaxial Layer Grown on On-Axis C-Face Substrate by CVD Method. *Materials Science Forum*, **2005**, 483-485, 93-96	0.4	6
35	Effects of Dislocations on Reliability of Thermal Oxides Grown on n-Type 4H-SiC Wafer. *Materials Science Forum*, **2005**, 483-485, 661-664	0.4	19
34	Defect Characterization of 4H-SiC Bulk Crystals Grown on Micropipe Filled Seed Crystals. *Materials Science Forum*, **2005**, 483-485, 315-318	0.4	
33	Lifetime Control of the Minority Carrier in PiN Diodes by He+ Ion Implantation. *Materials Science Forum*, **2005**, 483-485, 985-988	0.4	3
32	Impact ionization coefficients of 4H silicon carbide. *Applied Physics Letters*, **2004**, 85, 1380-1382	3.4	95
31	Reverse characteristics of pn diodes on 4H-SiC(000-1) C and (11-20) face. *Applied Physics Letters*, **2004**, 84, 1774-1776	3.4	11
30	Effects of n-type 4H-SiC epitaxial wafer quality on reliability of thermal oxides. *Applied Physics Letters*, **2004**, 85, 6182-6184	3.4	14
29	Dependence of acceptor levels and hole mobility on acceptor density and temperature in Al-doped p-type 4H-SiC epilayers. *Journal of Applied Physics*, **2004**, 96, 2708-2715	2.5	69
28	Effect of gate oxidation method on electrical properties of metal-oxide-semiconductor field-effect transistors fabricated on 4H-SiC C(0001) face. *Applied Physics Letters*, **2004**, 84, 2088-2090	3.4	132
27	Impact Ionization Coefficients of 4H-SiC. *Materials Science Forum*, **2004**, 457-460, 673-676	0.4	6
26	4H-SiC Carbon-Face Epitaxial Layers Grown by Low-Pressure Hot-Wall Chemical Vapor Deposition. *Materials Science Forum*, **2004**, 457-460, 209-212	0.4	2
25	Relationship between the Current Direction in the Inversion Layer and the Electrical Characteristics of Metal-Oxide-Semiconductor Field Effect Transistors on 3C-SiC. *Materials Science Forum*, **2004**, 457-460, 1405-1408	0.4	2

24	A Long-Term Reliability of Thermal Oxides Grown on n-Type 4H-SiC Wafer. *Materials Science Forum*, **2004**, 457-460, 1269-1274	0.4	4
23	Electrical Properties of pn Diodes on 4H-SiC(000-1) C-Face and (11-20) Face. *Materials Science Forum*, **2004**, 457-460, 1065-1068	0.4	2
22	4H-SiC MOSFETs on C(000-,1) Face with Inversion Channel Mobility of 127cm2/Vs. *Materials Science Forum*, **2004**, 457-460, 1417-1420	0.4	20
21	Direct observation of dislocations propagated from 4H-SiC substrate to epitaxial layer by X-ray topography. *Journal of Crystal Growth*, **2004**, 260, 209-216	1.6	161
20	Influence of growth conditions on basal plane dislocation in 4H-SiC epitaxial layer. *Journal of Crystal Growth*, **2004**, 271, 1-7	1.6	83
19	Homoepitaxial growth of 4H-SiC on on-axis C-face substrates by chemical vapor depositon. *Journal of Crystal Growth*, **2004**, 269, 367-376	1.6	52
18	Influence of C/Si Ratio on the 4H-SiC (0001) Epitaxial Growth and a Keynote for High-Rate Growth. *Materials Science Forum*, **2004**, 457-460, 213-216	0.4	12
17	The Electrical Characteristics of Metal-Oxide-Semiconductor Field Effect Transistors Fabricated on Cubic Silicon Carbide. *Japanese Journal of Applied Physics*, **2003**, 42, L625-L627	1.4	34
16	Uniformity of 4H-SiC epitaxial layers grown on 3-in diameter substrates. *Journal of Crystal Growth*, **2003**, 258, 113-122	1.6	6
15	N-channel MOSFETs fabricated on homoepitaxy-grown 3C-SiC films. *IEEE Electron Device Letters*, **2003**, 24, 466-468	4.4	32
14	Epitaxial Growth of High-Quality 4H-SiC Carbon-Face by Low-Pressure Hot-Wall Chemical Vapor Deposition. *Japanese Journal of Applied Physics*, **2003**, 42, L637-L639	1.4	56
13	Epitaxial Growth of (11-20) 4H-SiC Using Substrate Grown in the [11-20] Direction. *Materials Science Forum*, **2002**, 389-393, 195-198	0.4	5
12	A Large Reduction in Interface-State Density for MOS Capacitor on 4H-SiC (11-2 0) Face Using H2 and H2O Vapor Atmosphere Post-Oxidation Annealing. *Materials Science Forum*, **2002**, 389-393, 1057-1060	0.4	6
11	Replication of Defects from 4H-SiC Wafer to Epitaxial Layer. *Materials Science Forum*, **2002**, 389-393, 447-450	0.4	4
10	Significant Improvement of Inversion Channel Mobility in 4H-SiC MOSFET on (11-20) Face Using Hydrogen Post-Oxidation Annealing. *Materials Science Forum*, **2002**, 389-393, 1061-1064	0.4	9
9	Influence of the Crystalline Quality of Epitaxial Layers on Inversion Channel Mobility in 4H-SiC MOSFETs. *Materials Science Forum*, **2002**, 389-393, 1053-1056	0.4	1
8	High-Rate Epitaxial Growth of 4H-SiC Using a Vertical-Type, Quasi-Hot-Wall CVD Reactor. *Materials Science Forum*, **2002**, 389-393, 179-182	0.4	14
7	Distribution Profile of Deep Levels in SiC Observed by Isothermal Capacitance Transient Spectroscopy. *Materials Science Forum*, **2002**, 389-393, 851-854	0.4	

6	Investigation of Residual Impurities in 4H-SiC Epitaxial Layers Grown by Hot-Wall Chemical Vapor Deposition. *Materials Science Forum*, **2002**, 389-393, 215-218	0.4	6
5	Influence of stacking faults on the performance of 4H□SiC Schottky barrier diodes fabricated on (112 0) face. *Applied Physics Letters*, **2002**, 81, 2974-2976	3.4	22
4	Excellent effects of hydrogen postoxidation annealing on inversion channel mobility of 4H-SiC MOSFET fabricated on (11 2 0) face. *IEEE Electron Device Letters*, **2002**, 23, 13-15	4.4	83
3	Control of Surface Morphologies for Epitaxial Growth on Low Off-Angle 4H-SiC (0001) Substrates. *Materials Science Forum*, **2001**, 353-356, 135-138	0.4	4
2	Effects of Pyrogenic Reoxidation Annealing on Inversion Channel Mobility of 4H-SiC Metal-Oxide-Semiconductor Field-Effect Transistor Fabricated on $(11bar{2}0)$ Face. *Japanese Journal of Applied Physics*, **2001**, 40, L1201-L1203	1.4	10
1	Effects of Steam Annealing on Electrical Characteristics of 3C-SiC Metal-Oxide-Semiconductor Structures. *Materials Science Forum*, **2000**, 338-342, 1129-1132	0.4	